MIZORAM PUBLIC SERVICE COMMISSION

Competitive Examinations for Recruitment to the post of Inspector of Legal Metrology under Food, Civil Supplies & Consumer Affairs Department, Government of Mizoram, December, 2018

ELECTRONICS & COMMUNICATION ENGINEERING PAPER - I

Time Allowed: 2 hours Full Marks: 200 All questions carry equal marks of two (2) each. Attempt all questions. 1. Total number of electrons that can be accommodated in various electron states in a valence band of a given solid is equal to (a) The atomic number of the solid (b) Half the number of the atoms in the solid (d) Twice the number of the atoms in the solid (c) The number of atoms in the solid 2. Ionic bonding in solids depends primarily on (b) Sharing of electrons (a) Transfer of electrons (c) Electrical dipoles (d) All of these 3. One electron volt is equal to (b) 54.6×10^{-9} Joule (a) 1.6×10^{-19} Joule (c) 4.6×10^{-12} Joule (d) 1.3×10^{-7} Joule 4. Atomic number of Silicon is (a) 12 (b) 10 (c) 08 (d) 14 5. The bandgap of silicon at room temperature is (a) 1.1 eV (b) 6.6 eV (c) 0 eV (d) 9 eV **6.** At 0°K semiconductor materials have same structure as _____ except the difference in the size of band gap. (a) Metals (b) Semiconductors (c) Insulators (d) None of these 7. Which material is the semiconductor? (a) Al (b) Cu (c) Ge (d) SiO₂ **8.** The width of the energy band depends on which of the following?

(b) Pressure

(d) Mass of atom in the material

(a) Temperature

(c) Relative freedom of electrons in the crystal

9.	The material not having a negative temperature coefficient of resistivity are			
	(a)	Metals	(b)	Semiconductors
	(c)	Insulators	(d)	None of these
10.	Mate	rials, whose specific resistance abruptly falls a	ıt ver	ry low temperature, are called
	(a)	Conductors	(b)	Semiconductors
	(c)	Superconductors	(d)	Insulators
11.	A 'ho	ole' in a semiconductor has		
		i) Positive charge equal to the electron ch	arge	
		ii) Positive mass equal to the mass of the e	lectr	ron
		iii) An 'effective mass' greater than the 'eff	ectiv	e mass' of electron
		iv) Negative mass and positive charge equa	al to 1	the charge in nucleus
		ch of these statements are correct?		
	` ′	i, ii, iii, iv	` ′	i & iii only
	(c)	ii & iv only	(d)	iii & iv only
12.	Ferm	i level is the		
	` ′	Highest occupied energy level at 0 K		
		Highest occupied energy level at 0° C		
		Energy level at which electron emission occur	S	
	(d)	Minimum energy level in the conduction band		
13.	An ir	ntrinsic semiconductor has equal number of ele	ctror	ns and holes. This is due to
	(a)	Doping	(b)	Free electrons
	(c)	Thermal energy	(d)	Valance electrons
14.	With	an increase in temperature, the Fermi level in a	n int	rinsic semiconductor
	(a)	Move closer to the conduction band edge	(b)	Move closer to the valance band edge
	(c)	Move into the conduction band	(d)	Remains at the center of the forbidden gap
15.	Silico	on is not suitable for fabrication of light emittin	g dio	des because it is
	(a)	An indirect band gap semiconductor	(b)	A direct band gap semiconductor
	(c)	A wide band gap semiconductor		A narrow band gap semiconductor
16.	The 1	nobility of electrons in a semiconductor is defi	ned a	as the
		Diffusion velocity per unit electric field		Diffusion velocity per unit magnetic field
	` ′	Drift velocity per unit electric field	` ′	Drift velocity per unit magnetic field
17	The	diffusion current is proportional to		
17.		Applied electric field	(b)	Square of the electric field
		Concentration gradient of charge carrier	` ′	None of these
10			. ,	
18.		different categories of piezoelectric materials a		Commission and Outland anoun
		Natural group and Synthetic group Conducting group and Non conducting group	(b)	Ceramic group and Optical group
	(c)	Conducting group and Non conducting group	(u)	None of these
19.		e are two types of Ferrites, they are	. مر	
	` '	Soft Ferrites and Hard Ferrites	(b)	Simple Ferrites and Complex Ferrites
	(c)	Dark Ferrites and Light Ferrites	(d)	Back Ferrites and Front Ferrites

20.	The potential barrier existing across a P-N junction						
	(a) Prevents flow of minority carriers						
	(b)	Prevents neutralization of acceptor and donor	rions	3			
	(c) Prevents total recombination of holes and electrons						
	(d) Facilitates recombination of holes and electrons						
21.	With	the increase of reverse bias in a p-n diode, the	e reve	erse current			
	(a)	Decreases					
	(b)	Increases					
	(c)	Remains constant					
	(d)	May increase or decrease depending upon do	ping				
22.	Whic	th of the following is a "hot carrier diode"?					
	(a)	PIN diode	(b)	LED			
	(c)	Photo diode	(d)	Schottky diode			
23.	The t	ype of transistor preferred in IC technology is					
	(a)	pnp	(b)	pnpn			
	(c)	npn	(d)	pnp-npn			
24.	The c	current I _{CBO} flows in the					
	(a)	Emitter and base leads	(b)	Collector and base leads			
	(c)	Emitter and collector leads	(d)	None of these			
25.		ner regulator has an input voltage from 20 V to If the Zener voltage is 5 V, the value of series r					
	(a)	1 Kw	(b)	1.5 KW			
	(c)	1.66 KW	(d)	2.5 KW			
26.	5. Transistor is in saturation when						
	(a)	$I_B = I_C$	(b)	$I_{B} > \frac{I_{C}}{\beta_{dc}}$ $I_{B} < \frac{I_{C}}{\beta_{dc}}$			
				- I _C			
	(c)	$I_B = 0$	(d)	$I_B < \frac{-c}{\beta_{dc}}$			
27.	Early	effect is the modulation of effective base widt	h by				
	(a)	Emitter voltage	(b)	Emitter current			
	(c)	Collector voltage	(d)	Junction temperature			
28.	FET	is a device.					
	(a)	Unipolar	(b)	Bipolar			
	(c)	Tripolar	(d)	None of these			
29.	FET 1	terminals are:					
	(a)	Base, Emitter, Collector	(b)	Gate, Base, Bulk			
	(c)	Gate, Source, Base	(d)	Gate, Source, Drain			
30.	How	many layers of material does a transistor have	?				
	(a)	4	(b)	3			
	(c)	2	(d)	1			

31.	When	n the positive voltage on the gate of a p-channel	el JF	ET is increased, its drain current
	(a)	Increases	(b)	Decreases
	(c)	Remains the same	(d)	None of these
32.	MOS	SFET can be used as		
	(a)	Current controlled capacitor	(b)	Voltage controlled capacitor
	(c)	Current controlled inductor	(d)	Voltage controlled inductor
33.	Whic	ch of the following equipment can check the co	nditi	on of a transistor?
		Current tracer		Ohmmeter
	(c)	Digital display meter	(d)	All of these
34.	For w	what kind of amplifications can the active regio	n of t	the common-emitter configuration be used?
		Voltage		Current
	` /	Power	` /	All of these
25	. ,		()	
33.		nich region are both the collector-base and bas Active		Cutoff
	(a) (c)	Saturation	` /	Non-saturation
	. ,		()	
36.		er normal conditions a diode conducts current		
	` '	Reverse-biased	` /	Forward-biased
	(c)	Avalanched	(d)	Saturated
37.	An n-	-type semiconductor material		
	(a)	is intrinsic.	(b)	has trivalent impurity atoms added.
	(c)	has pentavalent impurity atoms added.	(d)	requires no doping.
38.	Effec	tively, how many valence electrons are there in	n eacl	n atom within a silicon crystal?
	(a)	2	(b)	4
	(c)	8	(d)	16
39.	The b	ooundary between p-type material and n-type i	nate	rial is called
	(a)	a diode.	(b)	a reverse-biased diode.
	(c)	a pn junction.	(d)	a forward-biased diode.
40.	An S	CR remains turned on if the anode current is n	nore	than the
		Breakdown current		Trigger current
	(c)	Holding current	(d)	Threshold current
41.	FET	has offset voltage of about		
11.		0.2 V	(b)	0.9 V
	` /	0.7 V	` /	0 V
12	. ,		()	
42.		ch of the following transistor is affected by stati		JFET
		npn Transistor	` /	
	` /	UJT	(d)	MOSFET
43.		e is a small amount of current across the barrier		
	` '	Forward-bias current	` ′	Reverse breakdown current
	(c)	Conventional current	(d)	Reverse leakage current

44. Analog signals can be converted into discrete-time signals by				
(a) S	Sampling	(b)	Quantizing	
(c) (Coding	(d)	Multiplexing	
45. δ (n) is	s equal to			
• •	u(n) + u(n-1)	(b)	u(n) - u(n-1)	
	u(n) * u(n-1)	` ′	u(n) + u(n-1) + u(n-2)	
46. The fu	ndamental period of a sinusoidal signal is	. ,		
,	2π			
(a)	$\overline{\omega_0}$	(b)	2π	
	_		ω_0	
(c) 2	$2\pi\omega_0$	(d)	$rac{\omega_0}{2\pi}$	
47. A signa	al is an energy signal if			
(a) H	E = 0, P = 0	(b)	$E = \infty, P < \infty$	
(c) H	$E < \infty, P = 0$	(d)	$E < \infty$, $P = \infty$	
48. A syste	em whose output depends on future inputs is	a		
-	Static system		Dynamic system	
` ´	Causal system		Linear system	
49. Fourier	er series applies to			
	Only periodic signals	(b)	Only aperiodic signals	
` ´	Both periodic and aperiodic signals	` ′	Only Random signals	
50. A sign	al $g(t) = A$ then $g(t)$ is a			
_	Energy signal	(b)	Power signal	
` '	Neither energy nor power signal	(d)	Insufficient data	
	pulse function consist of	,		
-	oure dc	(b)	pure ac	
· / I	nfinite bandwidth with linear phase variations	` ′	•	
, ,	gonometric Fourier series representation of a			
	Cosine term only		Sine term only	
` '	Both Sine and Cosine term	` ′	None	
. ,	equency spectrum of a periodic signal is	()		
	Continuous	(b)	Discrete	
` '	Both continuous and discrete	` /	None	
54. The type of systems which are characterized by input and the output quantized at certain levels				
are cal				
` '	Discrete	(b)	Analog	
(c) (Continuous	(d)	Digital	
55. A syste	55. A system which is linear is said to obey the rules of			
` ´	Scaling	` ′	Additivity	
(c) H	Both scaling and additivity	(d)	Homogeneity	

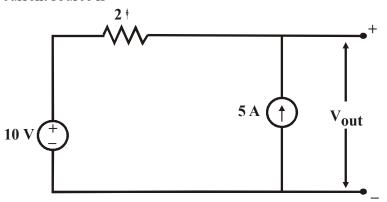
50.	A tın	ne invariant system is a system whose output					
	(a)	increases with a delay in input	(b)	decreases with a delay in input			
	(c)	remains same with a delay in input	(d)	vanishes with a delay in input			
57.	The f	frequency spectrum indicates					
	(a) The relative phase of each frequency components						
	(b)	The relative magnitude of each frequency con		ents			
	(c)	The relative frequency of each frequency con	-				
	(d)	None of these	1				
5 0							
50.		litortionless transmission, the amplitude and p					
	` '	Zero and Constant	` ′	Constant and Linear			
	(c)	Infinite and zero	(a)	Linear and zero			
59.	The	cross correlation of $x_1(t)$ and $x_2(t)$ is the same	as the	convolution of			
	(a)	$x_1(t)$ and $x_2(-t)$	(b)	$x_1(t)$ and $x_2(t)$			
	(c)	$x_1(-t)$ and $x_2(t)$	(d)	$x_1(-t)$ and $x_2(-t)$			
60.	The 1	nitial value of $L^{-1}\left[\frac{5}{S(S+2)}\right]$ is					
	(a)	0	(b)	5			
	(c)	∞	(d)	5/2			
61.	The	signal whose ROC is entire Z plane is					
011		d(n)	(b)	u(n)			
		r(n)	(d)	a ⁿ			
(2		• •	()				
62.		ROC of a stable system must include the	(1.)	T.C. '.			
		Origin	(b)	Infinity			
	(c)	Aring	(d)	Unit circle			
63.	Whi	ch of the following impulse response of LTI sy	stem	represents a stable system?			
	(a)	$h(t) = e^t \cos t u(t)$	(b)	$h(t) = e^t \sin t u(t)$			
	(c)	$h(t) = e^{-t} \cos t u(t)$	(d)	$h(t) = t \sin t u(t)$			
64.	The	differentiation of a unit impulse is,					
	(a)	Infinity	(b)	Zero			
	(c)	One	(d)	Two			
65.	Four	ier transform of cosW ₀ t is,					
00.	1001	101 transform 01 000m ₀ v 10,		1 1			
	(a)	$X(\Omega - \Omega_0) + X(\Omega + \Omega_0)$	(b)	$\frac{1}{2}X(\Omega - \Omega_0) + \frac{1}{2}X(\Omega + \Omega_0)$			
	(c)	$\pi[\delta(\Omega\!-\!\Omega_{_{\boldsymbol{0}}})\!+\!\delta(\Omega\!+\!\Omega_{_{\boldsymbol{0}}})]$	(d)	$\frac{\pi}{2}[X(\Omega-\Omega_0)+X(\Omega+\Omega_0)]$			
66.	Whe	n determining Thevenin's resistance of a circui	t				
		all sources must be open circuited					
		all sources must be short circuited					

(c) all voltage sources must be open circuited and all current sources must be short circuited

(d) all sources must be replaced by their internal resistances

67.	Thre value	e resistance of 15 W each are connected in dee of	lta. T	he resistance of equivalent star will have a
	(a)	7 W	(b)	5 W
	(c)	9 W	(d)	2 W
68.		C voltage source is connected across a series led DC voltage drops entirely across the	R-L-C	C circuit. Under steady state conditions, the
	` ′	Ronly	(b)	Lonly
	(c)	C only	(d)	R and L combination
69.	The	condition for the validity of Ohm's law is that	the	
	(a)	Temperature should be remain constant	(b)	Current should be proportional to the voltage
	(c)	Resistance must be wire wound type	(d)	All of these
70.	How	are 500W resistors connected so as to give a	n effe	ective resistance of 750W?
		Three resistors of 500W each, in parallel		
	(b)	Three resistors of 500W each, in series		
	(c)	Two resistors of 500W each, in parallel		
	(d)	Two resistors of 500W each, in parallel and the	e com	bination in series with another 500W resistor
71.	Two	bulbs of 100W/ 250 V and 150W/250 V are c	conne	cted in series across a supply of 250 V. The
		er consumed by the circuits is		11 7
	(a)	30 W	(b)	60 W
	(c)	100 W	(d)	250 W
72.	A cir	cuit having neither any energy source nor emf	sour	ce is called
		Unilateral circuit		Bilateral circuit
	(c)	Passive circuit	(d)	Active circuit
73.	Indu	ctance has the dimensions of		
,		Flux/current	(b)	Flux/length
	` ′	(Voltage)2/current	` ′	None of these
74.	A co	il of inductance 2H and resistance 1W is contance. The amount of energy stored in the mag	necte	d to a 10 V battery with negligible internal
		8 J		50 J
	(c)	25 J	(d)	100 J
75.		ch one of the following has the ability to act as frequency?	s an op	pen circuit for dc and a short circuit for ac of
	(a)	An insulator	(b)	A capacitor
	(c)	A resistor	(d)	None of these
76.	The	constant voltage source is		
		Active and bilateral	(b)	Passive and bilateral
	()	Active and unilateral	()	Passive and unilateral
77	. ,	current source have	` '	
, , ,		Zero internal resistance	(h)	Infinite internal resistance
	` ′	Low value of voltage	` '	Large value of current

78. In a circuit shown below, the voltage and current sources are ideal. The voltage (V_{out}) across the current source is



(a) 0 V

(b) 5 V

(c) 10 V

(d) 20 V

79. For a network of 11 branches and 6 nodes, what is the number of independent loops?

(a) 4

(b) 5

(c) 6

(d) 11

80. For any lumped network, for any cut sets and at any instant of time the algebraic sum of all branch currents traversing the cut-set branches is always

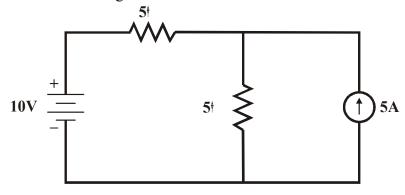
(a) One

(b) Zero

(c) Infinity

(d) Greater than zero, but less than one

81. What is the voltage across the current source for the below-shown circuit?



(a) 5 V

(b) 7.5 V

(c) 12.5 V

(d) 17.5 V

82. A 2-port network is represented by the following equation

$$I_1 = 5V_1 + 3V_2$$

 $I_2 = 2V_1 - 7V_2$

The value of Z_{12} is

(a) 3

(b) -3

(c) 3/41

(d) 2/31

83. Which of the following theorems can be applied to any network linear or non-linear, active or passive, time-variant or time-invariant?

(a) Thevenin's theorem

(b) Norton theorem

(c) Tellegen theorem

(d) Superposition theorem

84.	The low-frequency circuit impedance and the high-frequency circuit impedance for a series resonance circuit respectively are				
	(a) Capacitive and inductive	(b)	Inductive and capacitive		
	(c) Resistive and inductive	(d)	Capacitive and resistive		
85.	If the Q-factor of a coil at a resonant frequency of the corresponding bandwidth is	1.5 M	Hz is 150 for a series resonant circuit, then		
	(a) 225 MHz	(b)	1.06 MHz		
	(c) 50 KHz	(d)	10 KHz		
86.	A parallel circuit has two branches. In one branch and C are in series. The circuit will exhibit unity pe				
	(a) $R = \sqrt{\frac{L}{C}}$	(b)	$R = \sqrt{LC}$		
	(c) $R = \sqrt{\frac{C}{L}}$	(d)	$R = \frac{L}{C}$		
87.	In an intrinsic semiconductor, the Fermi level				
	(a) Lies at the center of forbidden energy gap	(b)	Is near the conduction band		
	(c) Is near the valence band	(d)	May be anywhere in the forbidden energy gap		
88.	3. The forbidden gap for germanium is				
	(a) 7.2 eV	(b)	0.72 eV		
	(c) 0.072 eV	(d)	72 eV		
89.	The process of adding impurities to a pure semiconductor is called				
	(a) Mixing	(b)	Doping		
	(c) Diffusing	(d)	All of these		
90.	n – type silicon is obtained by doping silicon with				
	(a) Germanium	(b)	Aluminum		
	(c) Boron	(d)	Phosphorus		
91.	Ferrites have				
	(a) Low copper loss	(b)	Low eddy current loss		
	(c) Low resistivity	(d)	High specific gravity compared to iron		
92.	Which material is used for making permanent mag	net?			
	(a) Carbon steel	(b)	Germanium		
	(c) Silicon	(d)	None of these		
93.	In a network containing active components, the output voltage				
	(a) Will always be greater than the input voltage				
	(b) Will always be equal to the input voltage				
	(c) Can be less than or greater than input voltag	•			
	(d) Will be less than, equal to or greater than the input voltage				

94.	94. The concentration of minority carriers in an extrinsic semiconductor under equilibrium is						
	(a) Directly proportional to the doping concentration.						
	(b) Inversely proportional to the doping concentration.						
	(c) Directly proportional to the intrinsic concentration.						
	(d) Inversely proportional to the intrinsic concentration.						
95.	. In an intrinsic Semiconductor the free electron concentration depends on						
	(a) Effective mass of electrons only						
	(b) Effective mass of holes only						
	(c)	Temperature of the Semiconductor					
	(d)	Width of the forbidden energy hand of the ser	nico	nductor			
96.	Two	Two-port networks are connected in cascade.	The c	combination is to the represented as a single			
	two-	port network, by multiplying the individual					
	(a)	z-parameter matrices	(b)	h-parameter matrices			
	(c)	y-parameter matrices	(d)	ABCD parameter			
97.	Wha	t happens to the resistance of a conductor if it	s len	gth is increased three times and diameter is			
	halved?						
	(a)	Resistance remains the same	(b)	Resistance is increased by 3 times			
	(c)	Resistance is increased by 6 times	(d)	Resistance is increased by 12 times			
98.	A pra	actical current source is represented by					
	(a)	A resistance in series with an ideal current so	urce				
	(b)	A resistance in parallel with an ideal current s	sourc	e			
	(c)	A resistance in parallel with an ideal voltage s	sourc	e			
	(d)	A resistance in series with an ideal voltage so	urce				
99.	How	much is the base-to-emitter voltage of a trans	istor	in the "on" state?			
		0 V		0.7 V			
	(c)	0.9 V	(d)	1.0 V			
100.	The I	Fourier series of an odd periodic function, con	tains	only			
	(a)	odd harmonics		even harmonics			
	(c)	cosine terms	(d)	sine terms			
		* * * *	k * *	**			
		* * * * *		•			
